

SMD Type

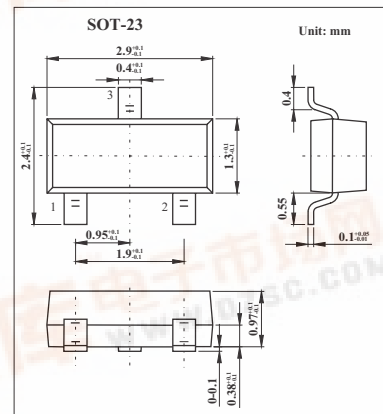
Diodes

Silicon PIN Diodes

BA779;BA779S

■ Features

- Wide frequency range 10 MHz to 1 GHz



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Test Conditions	Value	Unit
Reverse Voltage	V _R		30	V
Forward Current	I _F		50	mA
Junction Temperature	T _j		125	°C
Storage temperature range	T _{stg}		-55 to +125	°C
Junction ambient	R _{thJA}	on PC board 50mm×50mm×1.6mm	500	K/W

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	V _F	I _F = 20 mA			1	V
Reverse Current	I _R	V _R = 30 V			50	nA
Diode capacitance	C _D	f = 100 MHz, V _R = 0			0.5	pF
Differential forward resistance	r _f	f = 100 MHz, I _F = 1.5 mA			50	Ω
Reverse impedance	BA799	f = 100 MHz, V _R = 0	5			K Ω
	BA799S		9			
Minority carrier lifetime	τ	I _F = 10 mA, I _R = 10 mA		4		μ S